

In the Claims:

1-10. Cancelled.

11. (Currently Amended) ~~The method of Claim 1,~~ A method of producing a silicon carbide boule having a substantially single polytype, the method comprising:
forcing preferential nucleation sites on a surface of a silicon carbide seed crystal having the substantially single polytype to a predefined pattern; and
growing the silicon carbide boule utilizing physical vapor transport (PVT) so as to provide selective preferential growth of silicon carbide on the silicon carbide seed crystal corresponding to the predefined pattern;
wherein ~~the~~ forcing preferential nucleation sites comprises forming a pattern on ~~an exposed~~ the surface of the seed crystal so as to provide regions of the seed crystal which extend beyond other regions of the seed crystal; and
wherein forming a pattern comprises forming a pattern of sidewalls in the exposed surface of the seed crystal; and
wherein growing the silicon carbide boule comprises preferentially growing silicon carbide from the sidewalls.

12. (Original) The method of Claim 11, wherein the pattern comprises stripes in the seed crystal.

13. (Original) The method of Claim 11, wherein the pattern comprises a plurality of posts.

14. (Original) The method of Claim 13, wherein the posts are substantially circular.

15. Cancelled.

16. (Currently Amended) ~~The method of Claim 1,~~ A method of producing a silicon carbide boule having a substantially single polytype, the method comprising:

forcing nucleation sites on a surface of a silicon carbide seed crystal having the substantially single polytype to a predefined pattern; and

growing the silicon carbide boule utilizing physical vapor transport (PVT) so as to provide selective preferential growth of silicon carbide on the silicon carbide seed crystal corresponding to the predefined pattern;

wherein forcing nucleation sites comprises forming a pattern of material other than silicon carbide on a surface of the silicon carbide seed crystal thereby selectively exposing portions of the seed crystal to define the nucleation sites in the selectively exposed portions of the seed crystal;

wherein the pattern of material other than silicon carbide provides a pattern of regions having a reduced sticking coefficient than that of the exposed portions of the seed crystal; and

wherein the silicon carbide boule grows laterally above the material other than silicon carbide.

17. (Original) The method of Claim 16, wherein the pattern comprises stripes on the seed crystal.

18. (Original) The method of Claim 16, wherein the pattern comprises a plurality of posts on the seed crystal.

19. (Previously Presented) The method of Claim 16, wherein the pattern comprises a layer of material having a plurality of openings therein so as to expose portions of the seed crystal.

20. (Original) The method of Claim 19, wherein the openings are substantially circular.

21. (Original) The method of Claim 16, wherein the material other than silicon carbide comprises graphite.

22-56. Cancelled.